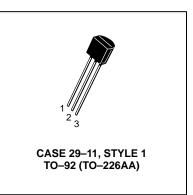
Amplifier Transistor PNP Silicon

MAXIMUM RATINGS

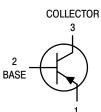
Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	V _{CEO}	-100	Vdc	
Collector–Base Voltage	V _{CBO}	-100	Vdc	
Emitter-Base Voltage	V _{EBO}	-4.0	Vdc	
Collector Current — Continuous	۱ _C	-600	mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C	



MPSL51

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



EMITTER

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

Characteristic		Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = -1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	-100	_	Vdc
Collector–Base Breakdown Voltage $(I_C = -100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	-100	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-4.0	_	Vdc
Collector Cutoff Current ($V_{CB} = -50 \text{ Vdc}, I_E = 0$)	I _{CBO}	_	-1.0	μAdc
Emitter Cutoff Current ($V_{EB} = -3.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	—	-100	nAdc

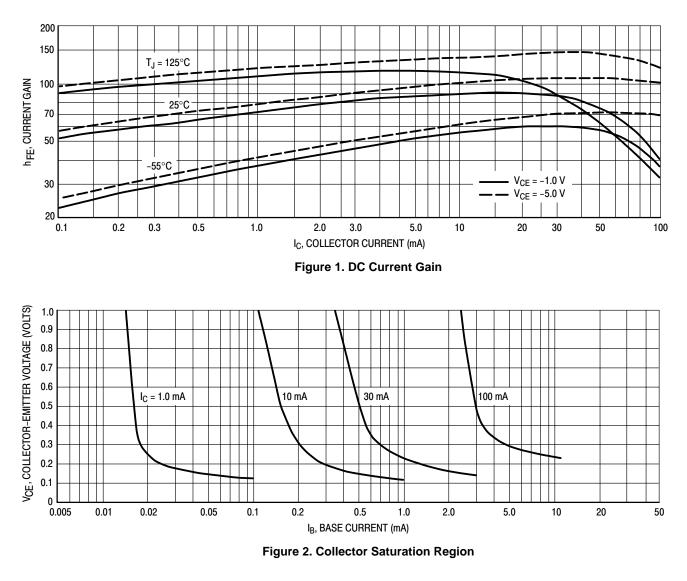
1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2.0%.

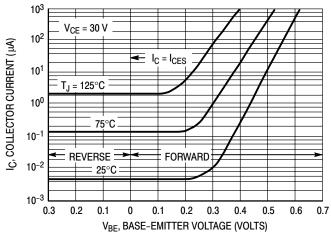


ELECTRICAL CHARACTERISTICS (T _A =	25°C unless otherwise noted) (Continued)
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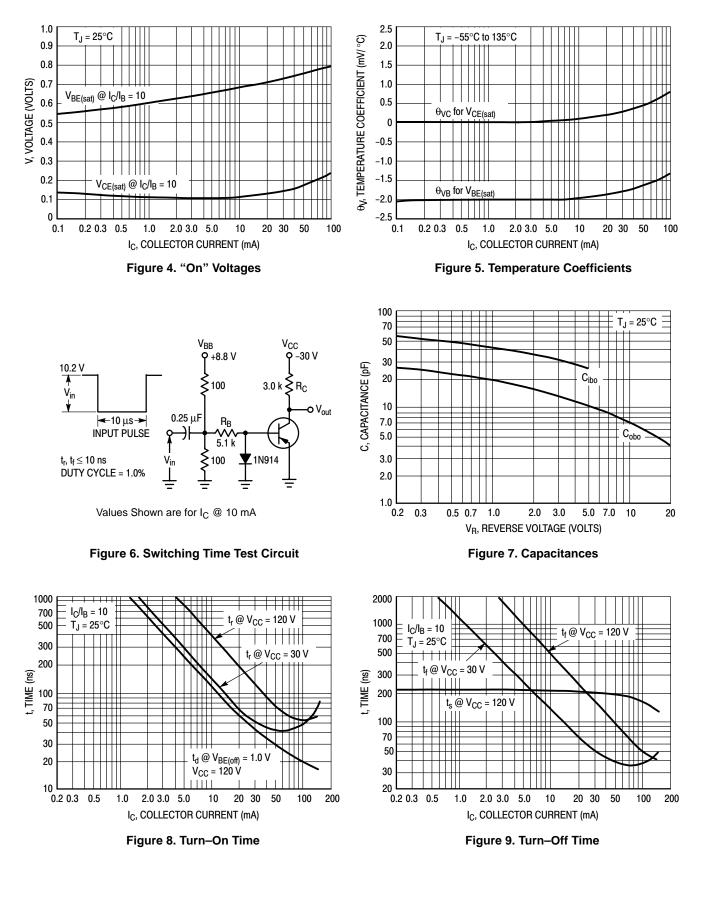
Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS ⁽¹⁾				
DC Current Gain ⁽¹⁾ (I _C = -50 mAdc, V _{CE} = -5.0 Vdc)	h _{FE}	40	250	—
Collector-Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	_	-0.25 -0.30	Vdc
Base-Emitter Saturation Voltage $(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$ $(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$	V _{BE(sat)}		-1.2 -1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product (I _C = –10 mAdc, V _{CE} = –10 Vdc, f = 20 MHz)	fT	60	—	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Small–Signal Current Gain (I _C = −1.0 mAdc, V _{CE} = −10 Vdc, f = 1.0 kHz)	h _{fe}	20	_	_

1. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle = 2.0%.



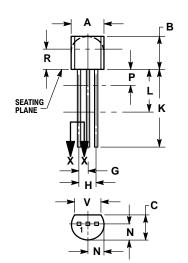






PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 29-11 ISSUE AL





STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

<u>Notes</u>

<u>Notes</u>

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